



DMT4011LFG

POWERDI

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _C = +25°C
	11.5mΩ @ V _{GS} = 10V	30A
40V	17.8mΩ @ V _{GS} = 4.5V	24A

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

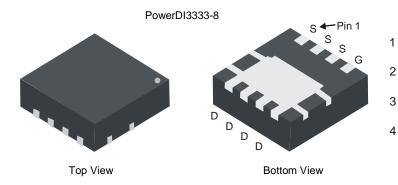
- Low R_{DS(ON)} Ensures On State Losses Are Minimized
- Excellent Q_{gd x} R_{DS(ON)} Product (FOM)
- Advanced Technology for DC-DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products

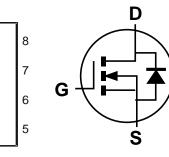
N-CHANNEL ENHANCEMENT MODE MOSFET

- 100% UIS (Avalanche) Rated
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.008 grams (Approximate)





Top View Internal Schematic

Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT4011LFG-7	PowerDI3333-8	2,000/Tape & Reel
DMT4011LFG-13	PowerDI3333-8	3,000/Tape & Reel

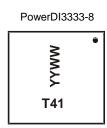
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



T41 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 16 = 2016) WW = Week Code (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	40	V	
Gate-Source Voltage	V _{GSS}	+20 -16	V	
Continuous Drain Current (Note 5) V_{GS} = 10V	T _C = +25°C T _C = +70°C	ID	30 24	A
Continuous Drain Current (Note 5) V _{GS} = 10V	T _A = +25°C T _A = +70°C	ID	10.8 8.6	A
Maximum Continuous Body Diode Forward Current (Note 5)	Is	2.1	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	65	А	
Avalanche Current, L=0.3mH	I _{AS}	11.9	А	
Avalanche Energy, L=0.3mH	E _{AS}	21.4	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{ extsf{ heta}JA}$	62	°C/W
Total Power Dissipation (Note 5) T _C = +25°C		PD	15.6	W
Thermal Resistance, Junction to Case (Note 5)		R _θ JC	8	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)	1 -						
Drain-Source Breakdown Voltage	BV _{DSS}	40	-	-	V	$V_{GS} = 0V, I_{D} = 1mA$	
Zero Gate Voltage Drain Current	IDSS	-	-	1	μA	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	100 -100	nA	$V_{GS} = +20V, V_{DS} = 0V$ $V_{GS} = -16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		-	9.2	11.5	mΩ	$V_{GS} = 10V, I_D = 20A$	
	R _{DS(ON)}	-	13.4	17.8		$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	V _{SD}	-	-	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss	-	767	-		$V_{DS} = 20V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	C _{oss}	-	238	-	pF		
Reverse Transfer Capacitance	C _{rss}	-	30.6	-			
Gate Resistance	R _g	-	1	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	7	-			
Total Gate Charge (V _{GS} = 10V)	Qg	-	15.1	-	nC	$V_{DS} = 20V, I_D = 20A$	
Gate-Source Charge	Q _{gs}	-	2.1	-	nc		
Gate-Drain Charge	Q _{gd}	-	3.2	-			
Turn-On Delay Time	t _{D(ON)}	-	3.5	-			
Turn-On Rise Time	t _R	-	5.8	-		$V_{DD} = 20V, V_{GS} = 10V,$ $R_G = 1.6\Omega, I_D = 20A$	
Turn-Off Delay Time	t _{D(OFF)}	-	9.6	-	ns		
Turn-Off Fall Time	t _F	-	2	-			
Body Diode Reverse Recovery Time	t _{RR}	-	9.8	-	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	-	5.1	-	nC	— I _F = 15A, di/dt = 400A/μs	

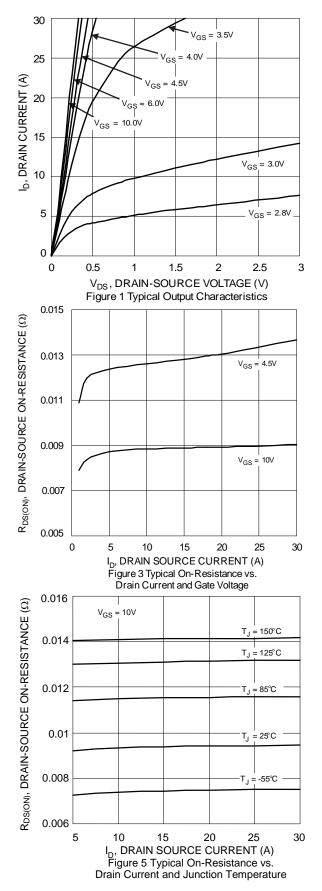
Notes: 5. R_{0JA} is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout. R_{0JC} is guaranteed by design while R_{0JA} is determined by the user's board design.

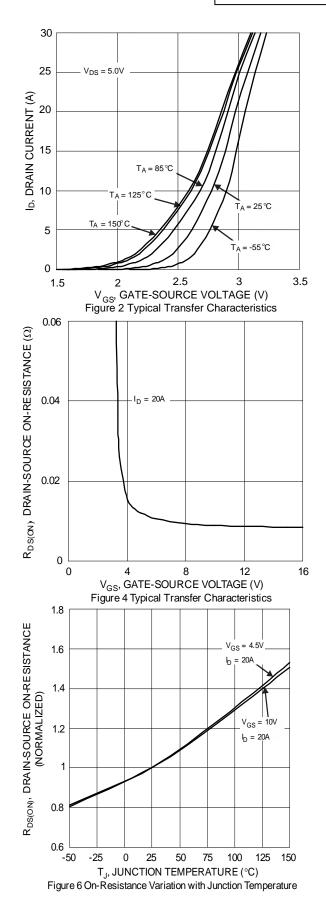
6. Short duration pulse test used to minimize self-heating effect.

7. Guaranteed by design. Not subject to product testing.

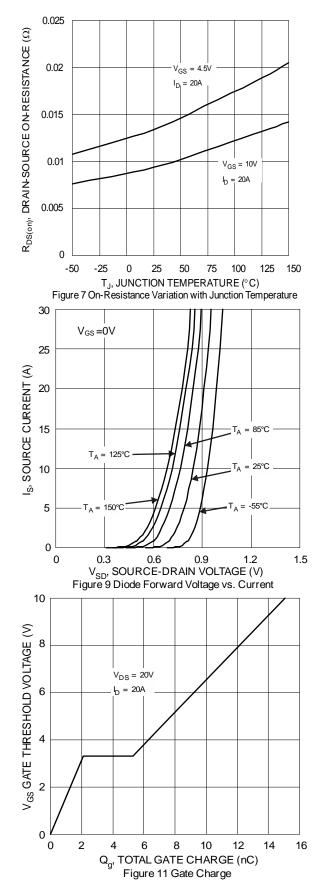


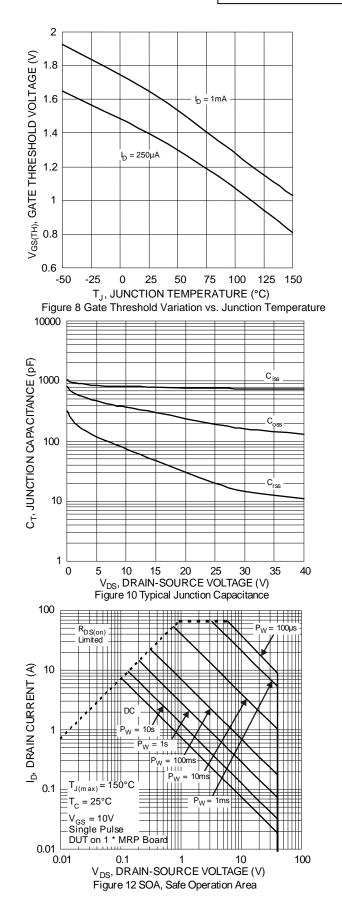
DMT4011LFG



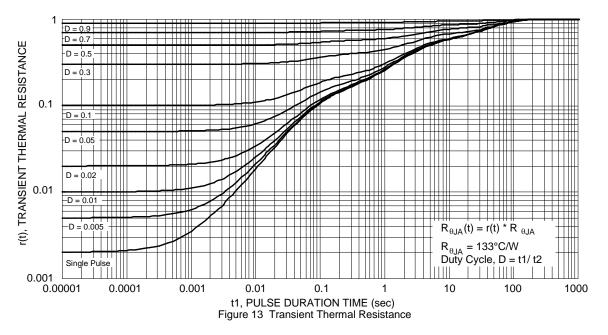








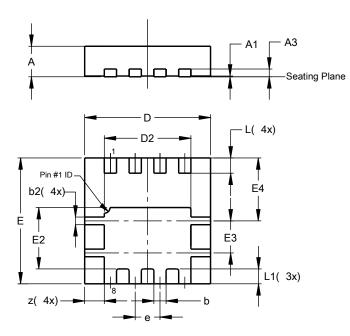






Package Outline Dimensions

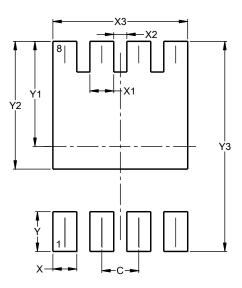
Please see http://www.diodes.com/package-outlines.html for the latest version.



PowerDI3333-8					
Dim	Min	n Max Ty			
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	-	-	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
ш	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
e	-	-	0.65		
L	0.35	0.45	0.40		
L1	_	-	0.39		
z	_	_	0.515		
All I	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



PowerDI3333-8

PowerDI3333-8

Dimensions	Value (in mm)			
С	0.650			
Х	0.420			
X1	0.420			
X2	0.230			
X3	2.370			
Y	0.700			
Y1	1.850			
Y2	2.250			
Y3	3.700			



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